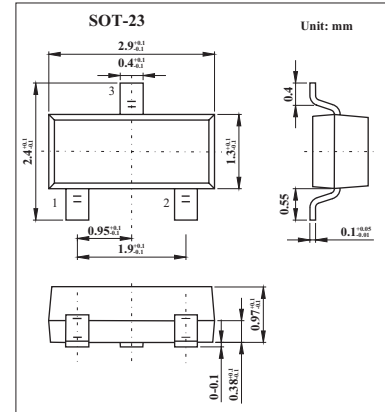
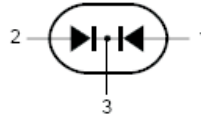


High-Speed Double Diode

1PS184

■ Features

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 80 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	VRRM	85	V
Continuous reverse voltage	VR	80	V
Continuous forward current (single diode loaded *) (double diode loaded *)	IF	215 125	mA
Repetitive peak forward current	IFRM	500	mA
Non-repetitive peak forward current Tj=25 °C t=1 μs t=1s	IFSM	4 0.5	A
power dissipation *	PD	250	mW
Thermal resistance from junction to tie-point	Rth j-tp	250	K/W
Thermal resistance from junction to ambient *	Rth j-a	500	K/W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-65 to +150	°C

* Device mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 1 mA		610		mV
		IF = 10 mA		740		mV
		IF = 50 mA			1.0	V
		IF = 100 mA			1.2	V
Reverse current	IR	VR = 25 V			30	nA
		VR = 80 V			0.5	μA
		VR = 25 V; Tj = 150 °C			30	μA
		VR = 80 V; Tj = 150 °C			100	μA
Diode capacitance	Cd	VR = 0 V, f = 1 MHz			1.5	pF
Reverse recovery time	trr	when switched from IF = 10 mA to IR = 10 mA; RL = 100 Ω; measured at IR = 1 mA			4	nS
Forward recovery voltage	Vfr	IF = 10 mA, tr = 20 ns			1.75	V

■ Marking

Marking	B3T